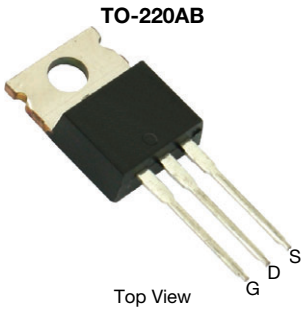
P-Channel 60 V (D-S) MOSFET



Top View

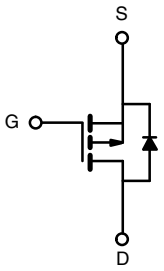
FEATURES

- TrenchFET® power MOSFET
- 100 % UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT

APPLICATIONS

- Load switch



P-Channel MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	-60
$R_{DS(on)}$ max. (Ω) at V_{GS} = -10 V	0.0195
$R_{DS(on)}$ max. (Ω) at V_{GS} = -4.5 V	0.0250
Q_g typ. (nC)	76
I_D (A) [a]	-53
Configuration	Single

ORDERING INFORMATION	
Package	TO-220AB
Lead (Pb)-free	SUP53P06-20-E3

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V_{DS}	-60	V
Gate-source voltage		V_{GS}	± 20	
Continuous drain current (T_J = 150 °C)	T_C = 25 °C	I_D	-53 [a]	A
	T_C = 70 °C		-46.8	
	T_A = 25 °C		9.2 [b]	
	T_A = 70 °C		-8.1 [b]	
Pulsed drain current		I_{DM}	-150	
Avalanche current pulse	L = 0.1 mH	I_{AS}	-45	
Single pulse avalanche energy		E_{AS}	101	mJ
Continuous source-drain diode current	T_C = 25 °C	I_S	69 [a]	A
	T_A = 25 °C		2.1 [b]	
Maximum power dissipation	T_C = 25 °C	P_D	104.2 [a]	W
	T_C = 70 °C		66.7 [a]	
	T_A = 25 °C		3.1 [b]	
	T_A = 70 °C		2 [b]	
Operating junction and storage temperature range		T_J, T_{stg}	-55 to +150	°C

THERMAL RESISTANCE RATINGS

PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient [b]	Steady state	R_{thJA}	33	40	°C/W
Maximum junction-to-case	Steady state	R_{thJC}	0.98	1.2	

Notes

a. Based on T_C = 25 °C

b. Surface mounted on 1" x 1" FR4 board

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-source breakdown voltage	V_{DS}	V_{GS} = 0 V, I_D = -250 µA	-60	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	I_D = -250 µA	-	68	-	mV/°C
$V_{GS(th)}$ temperature coefficient	$\Delta V_{GS(th)}/T_J$		-	-5.2	-	
Gate-source threshold voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250 µA	-1	-	-3	V
Gate-source leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V	-	-	± 100	nA
Zero gate voltage drain current	I_{DSS}	V_{DS} = -60 V, V_{GS} = 0 V	-	-	-1	µA
		V_{DS} = -60 V, V_{GS} = 0 V, T_J = 55 °C	-	-	-10	
On-state drain current [a]	$I_{D(on)}$	V_{DS} = -5 V, V_{GS} = -10 V	-120	-	-	A
Drain-source on-state resistance [a]	$R_{DS(on)}$	V_{GS} = -10 V, I_D = -30 A	-	0.0160	0.0195	Ω
		V_{GS} = -4.5 V, I_D = -20 A	-	0.0200	0.0250	
Forward transconductance [a]	g_{fs}	V_{DS} = -15 V, I_D = -50 A	20	-	-	S
Dynamic [b]						
Input capacitance	C_{iss}	V_{DS} = -25 V, V_{GS} = 0 V, f = 1 MHz	-	3500	-	pF
Output capacitance	C_{oss}		-	390	-	
Reverse transfer capacitance	C_{rss}		-	290	-	
Total gate charge	Q_g	V_{DS} = -30 V, V_{GS} = -10 V, I_D = -55 A	-	76	115	nC
		V_{DS} = -30 V, V_{GS} = -4.5 V, I_D = -55 A	-	38	60	
Gate-source charge	Q_{gs}		-	16	-	
Gate-drain charge	Q_{gd}		-	19	-	
Gate resistance	R_g	f = 1 MHz	-	5.2	-	Ω
Turn-on delay time	$t_{d(on)}$	V_{DD} = -2 V, R_L = 2 Ω $I_D \cong$ -10 A, V_{GEN} = -10 V, R_g = 1 Ω	-	10	15	ns
Rise time	t_r		-	7	15	
Turn-off delay time	$t_{d(off)}$		-	70	110	
Fall time	t_f		-	40	60	
Drain-Source Body Diode Characteristics						
Continuous source-drain diode current	I_S	T_C = 25 °C	-	-	-69	A
Pulse diode forward current [a]	I_{SM}		-	-	-150	
Body diode voltage	V_{SD}	I_S = -30 A	-	-1	-1.5	V
Body diode reverse recovery time	t_{rr}	I_F = -50 A, di/dt = 100 A/µs, T_J = 25 °C	-	45	68	ns
Body diode reverse recovery charge	Q_{rr}		-	59	120	nC
Reverse recovery fall time	t_a		-	29	-	ns
Reverse recovery rise time	t_b		-	16	-	

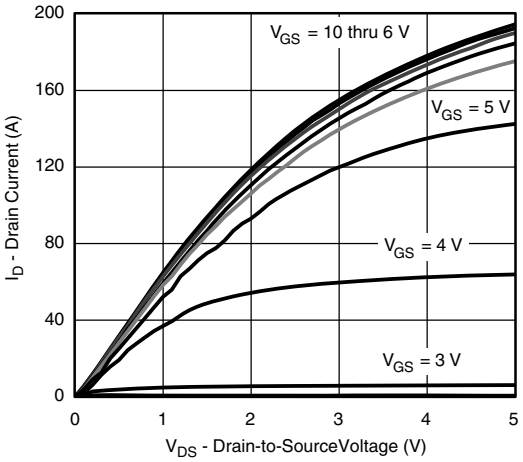
Notes

a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %

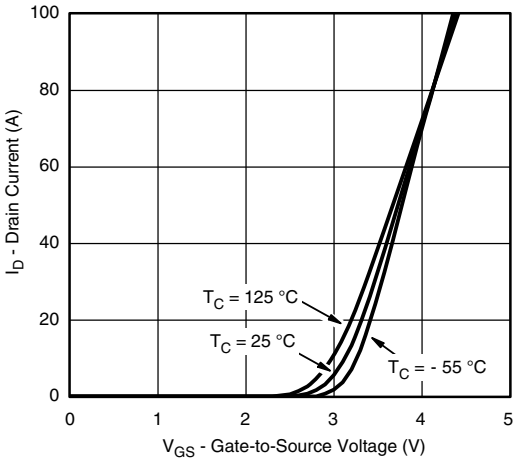
b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

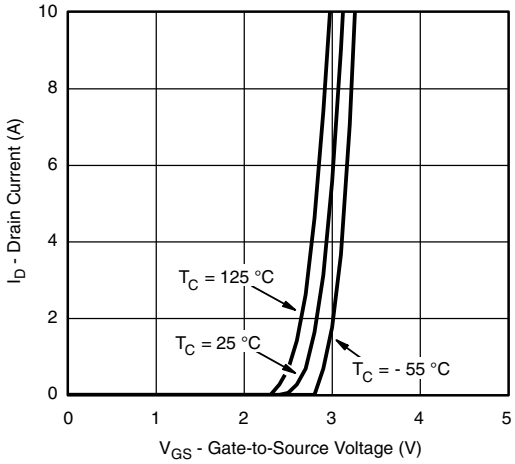
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



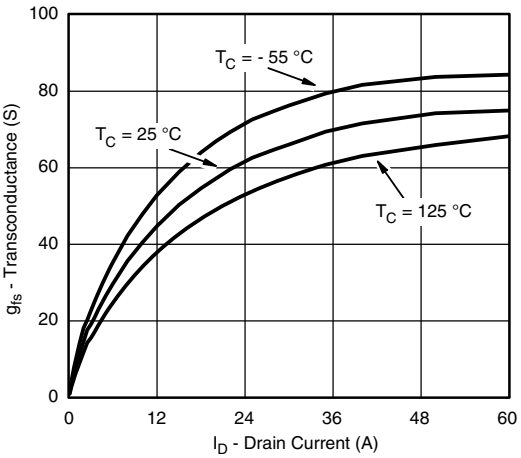
Output Characteristics



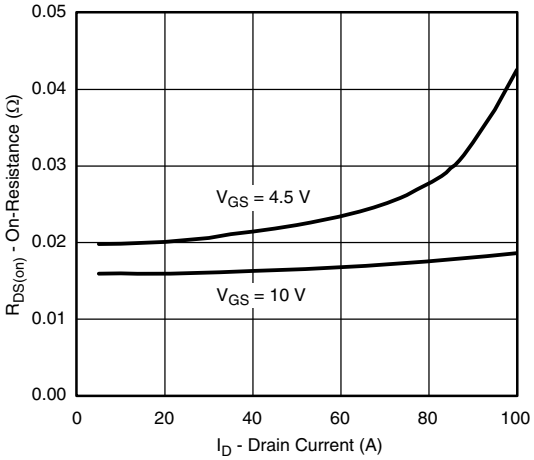
Transfer Characteristics



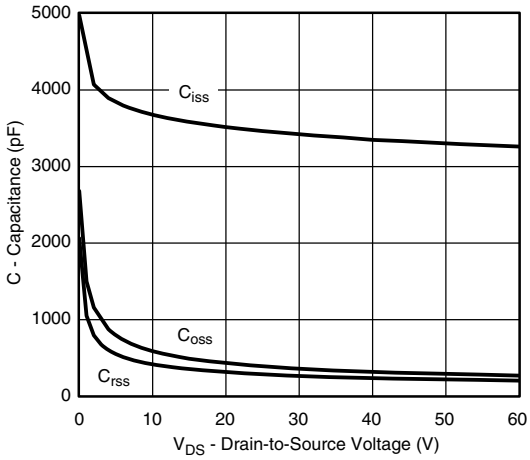
Transfer Characteristics



Transconductance

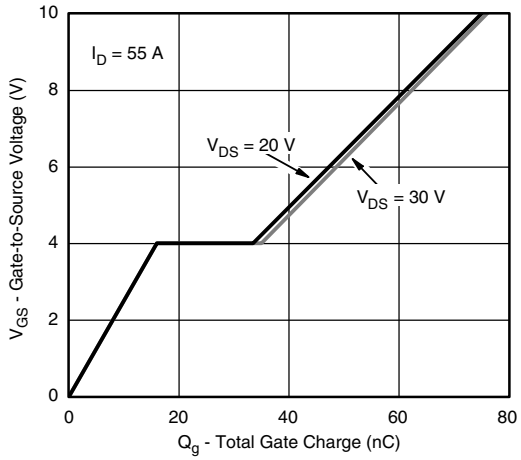


On-Resistance vs. Drain Current

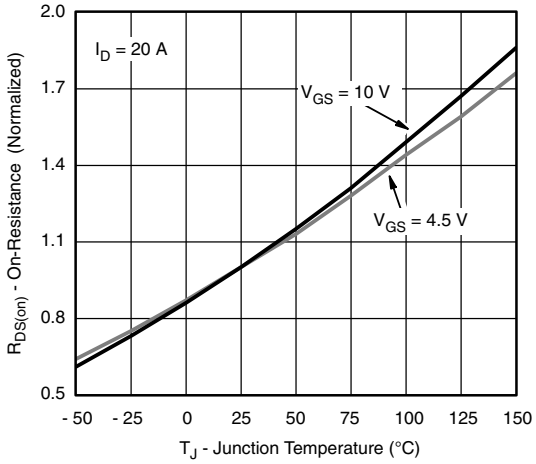


Capacitance

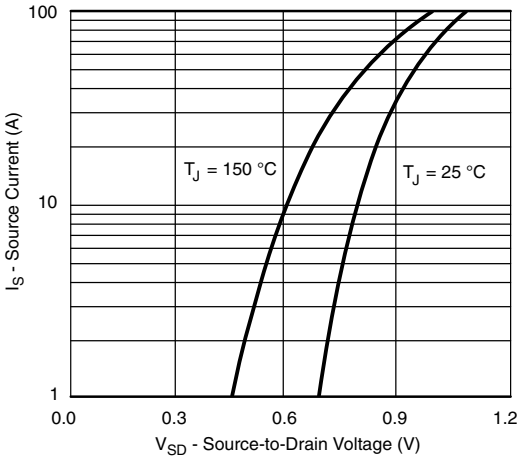
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



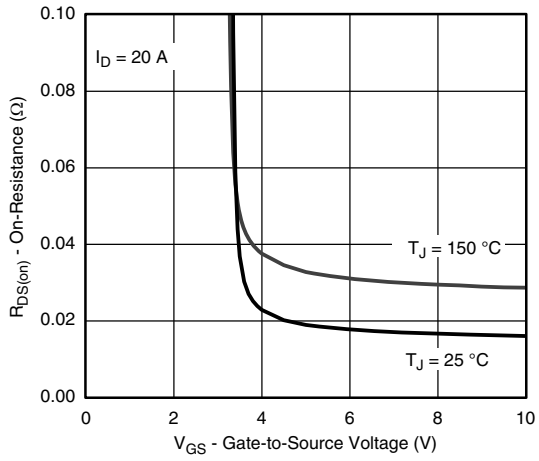
Gate Charge



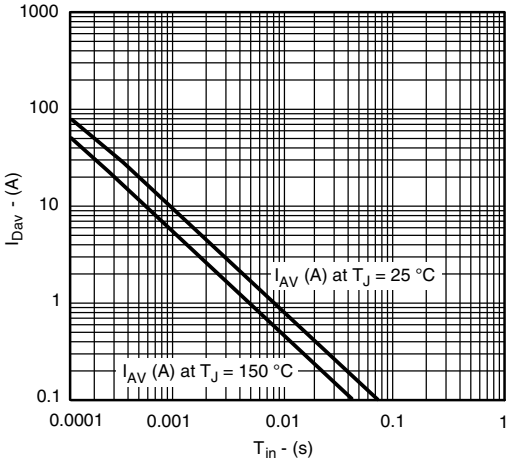
On-Resistance vs. Gate-to-Source Voltage



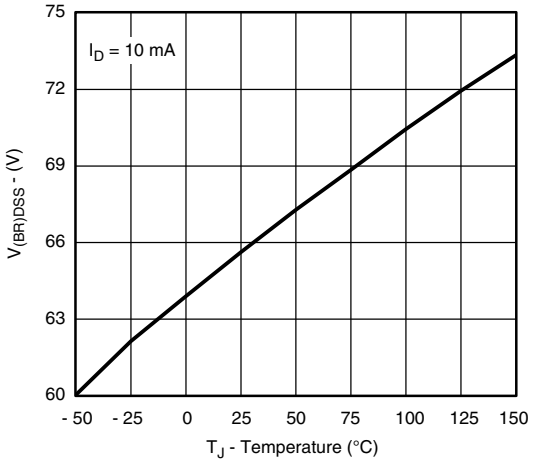
Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage

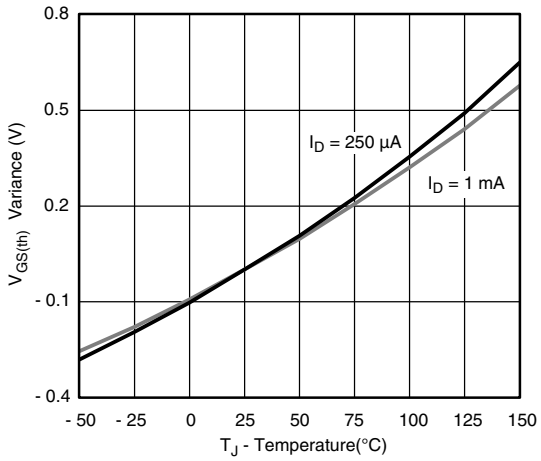


Single Pulse Avalanche Current Capability vs. Time

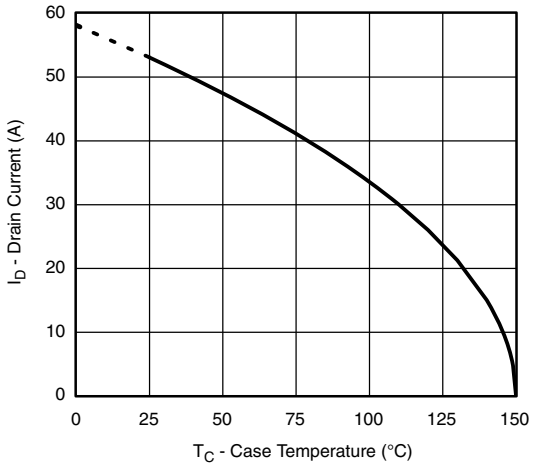


Drain-Source Breakdown Voltage vs. Junction Temperature

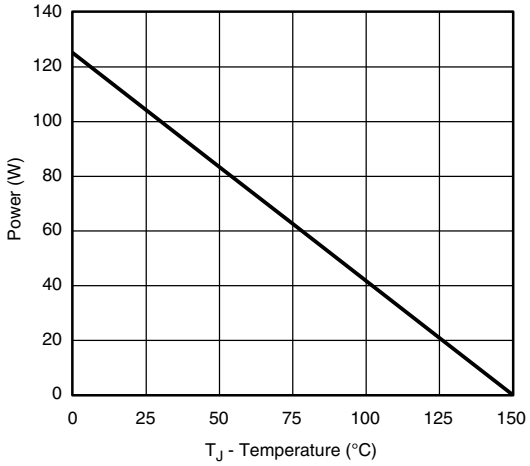
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



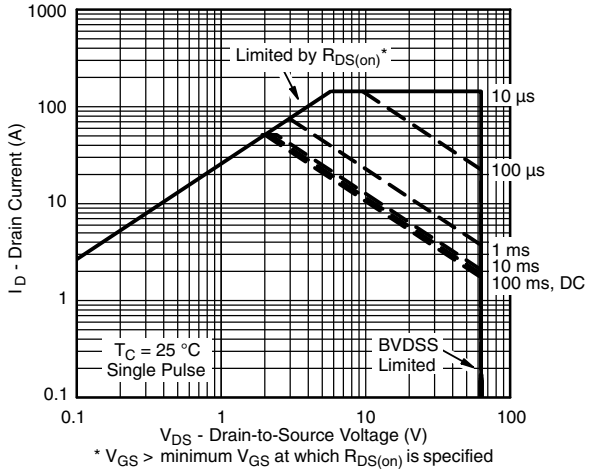
Threshold Voltage



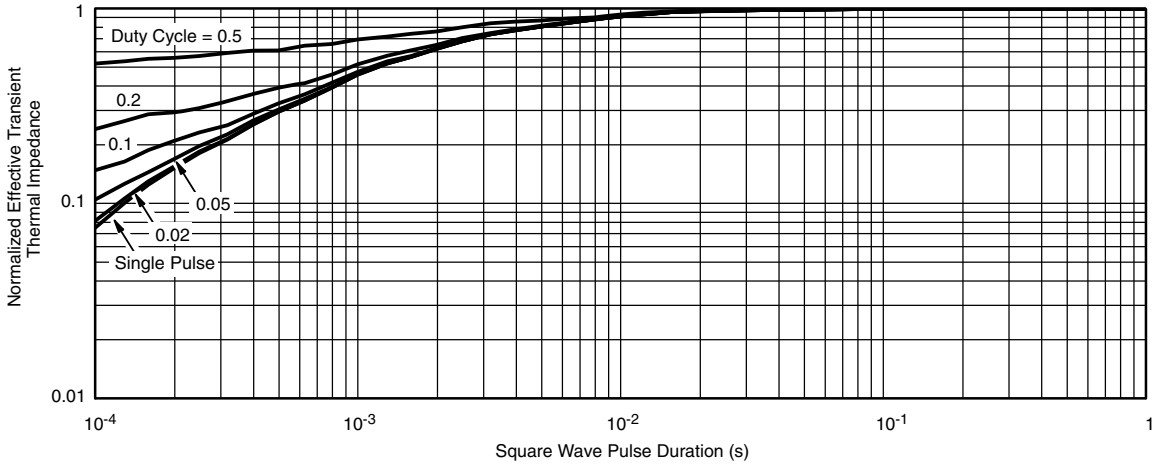
Max. Drain Current vs. Case Temperature



Power Derating, Junction-to-Case



Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Case

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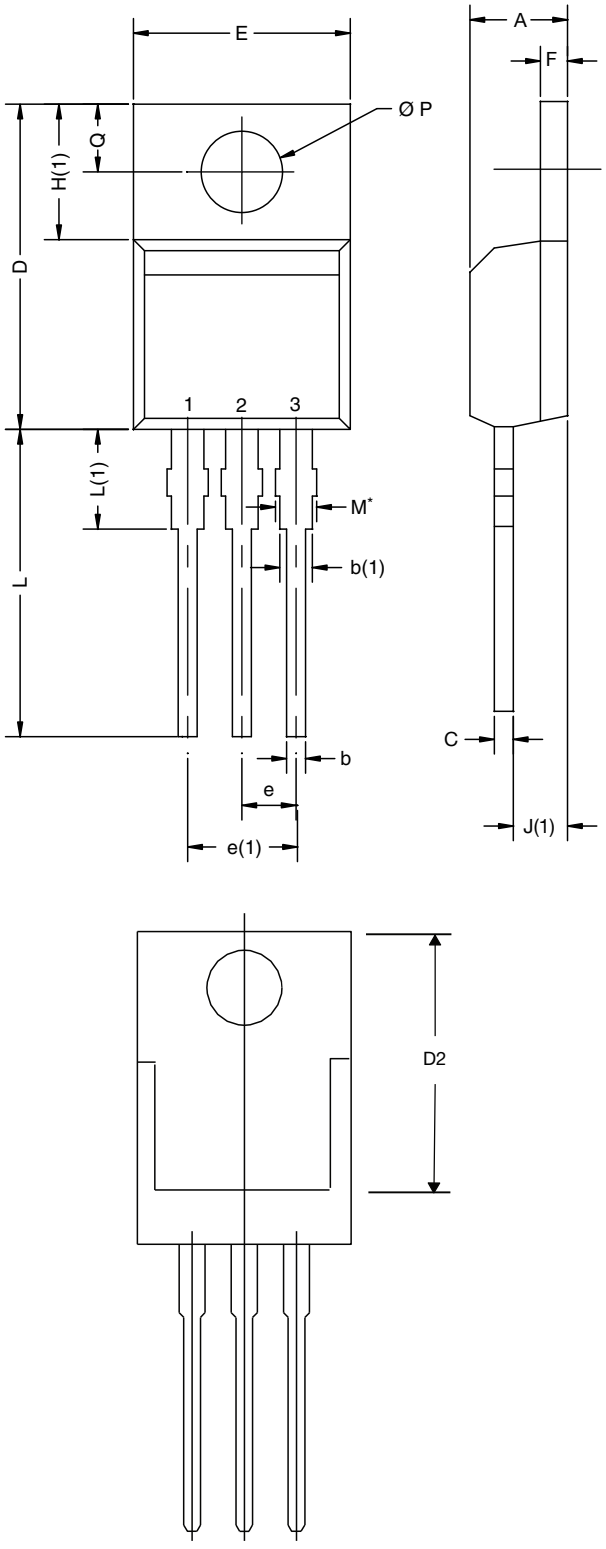
TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
c	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
D2	12.19	12.70	0.480	0.500
E	10.04	10.51	0.395	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
Ø P	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118
ECN: T14-0413-Rev. P, 16-Jun-14 DWG: 5471				

Note

* M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM

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